

## NSBC115TPDP6T5G

#### NSBC115TPDP6T5G Information

unvie televener.com	 NSBC115TPDP6T5G ON Semiconductor Discrete Semiconductor Products Transistors - Bipolar (BJT) - Arrays, Pre-Biased TRANS NPN/PNP PREBIAS SOT963 SOT-963 For the pricing/inventory/lead time, please contact	
For Reference Only	us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

#### **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.



### NSBC115TPDP6T5G Specifications

Manufacturer Part NumberNSBC115TPDP6T5GManufacturerON SemiconductorCategoryDiscrete Semiconductor ProductsTransitors - Bipolar (BJT) - Arrays, Pre-BiasedPackageSOT-963Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)100kResistor - Base (R2) (Ohms)-Vc Saturation (Max) @ Ib, Ic250mV@ 1mA, 10mAVce Saturation (Max) @ Ib, Ic500nACurrent - Collector Cutoff (Max)500nAFrequency - Transition-Power - Max339mW			
CategoryDiscrete Semiconductor ProductsCategoryDiscrete Semiconductor ProductsTransistors - Bipolar (BJT) - Arrays, Pre-BiasedPackageSOT-963Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Lo (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)100kResistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Lc, Vce160 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nA	Manufacturer Part Number	NSBC115TPDP6T5G	
InterferenceTransistor - Bipolar (BJT) - Arrays, Pre-BiasedPackageSOT-963Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Lc) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)100kResistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Lc, Vce160 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nA	Manufacturer	ON Semiconductor	
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Series-Transistor Type1 NPN, 1 PNP - Pre-Biased (Dual)Current - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)100kResistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Ic, Vce160 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-		Transistors - Bipolar (BJT) - Arrays, Pre-Biased	
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Current - Collector (Ic) (Max)100mAVoltage - Collector Emitter Breakdown (Max)50VResistor - Base (R1) (Ohms)100kResistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Ic, Vce160 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-	Series	-	
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Resistor - Base (R1) (Ohms)100kResistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Ic, Vce160 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-	Current - Collector (Ic) (Max)	100mA	
Resistor - Emitter Base (R2) (Ohms)-DC Current Gain (hFE) (Min) @ Ic, Vce160 @ 5mA, 10VVce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-	Voltage - Collector Emitter Breakdown (Max)	50V	
DC Current Gain (hFE) (Min) @ Ic, Vce 160 @ 5mA, 10V   Vce Saturation (Max) @ Ib, Ic 250mV @ 1mA, 10mA   Current - Collector Cutoff (Max) 500nA   Frequency - Transition -	Resistor - Base (R1) (Ohms)	100k	
Vce Saturation (Max) @ Ib, Ic250mV @ 1mA, 10mACurrent - Collector Cutoff (Max)500nAFrequency - Transition-	Resistor - Emitter Base (R2) (Ohms)	-	
Current - Collector Cutoff (Max)500nAFrequency - Transition-	DC Current Gain (hFE) (Min) @ Ic, Vce	160 @ 5mA, 10V	
Frequency - Transition -	Vce Saturation (Max) @ Ib, Ic	250mV @ 1mA, 10mA	
	Current - Collector Cutoff (Max)	500nA	
Power - Max 339mW	Frequency - Transition	-	
	Power - Max	339mW	
Mounting Type Surface Mount	Mounting Type	Surface Mount	
Package / Case SOT-963	Package / Case	SOT-963	
Supplier Device Package SOT-963	Supplier Device Package	SOT-963	
Report errors?		Report errors?	

#### NSBC115TPDP6T5G Guarantees



**Quality Guarantees** 

We provide 90 days warranty. \* If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

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#### **Service Guarantees**

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

#### NSBC115TPDP6T5G Payment Methods





If you have any question about NSBC115TPDP6T5G, please do not hesitate to contact us! Website: https://www.heisener.com E-mail: salesdept@heisener.com